



Product Overview

NTLJF3117P: Power MOSFET -20V -4.1A 100 mOhm Single P-Channel WDFN-6 FETky

For complete documentation, see the data sheet

Product Description

Power MOSFET and Schottky Diode, -20 V, -4.1 A, P-Channel, with 2.0 A Schottky Barrier Diode, 2x2 mm, μ Cool™ Product Family

Features

- FETKY™ Configuration with MOSFET plus Low Vf Schottky Diode
- μ Cool™ Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- 2x2 mm Footprint Same as SC-88 Package Design
- Independent Pinout Provides Circuit Design Flexibility
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environment
- High Current Schottky Diode: 2 A Current Rating
- This is a Pb-Free Device

Applications

- Optimized for Portable Applications like Cell Phones, Digital Cameras, Media Players, etc.
- DC-DC Buck Circuit
- Li-Ion Battery Applications
- Color Display and Camera Flash Regulators

End Products

- Media Players

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS(sat)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$r_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 10$ V (m)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	Q_{gd} Typ @ $V_{GS} = 4.5$ V (nC)	Q_{rr} Typ (nC)	C_{iss} Typ (pF)	C_{oss} Typ (pF)	C_{rss} Typ (pF)	Package Type
NTLJF3117PT1G	Pb-free Halide free	Active	P-Channel	with Schottky Diode	20	8	1	4.1	2.3	135	100		5.5			5.7	531	91	56	WDFN-6

For more information please contact your local sales support at www.onsemi.com

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